

TO-252 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

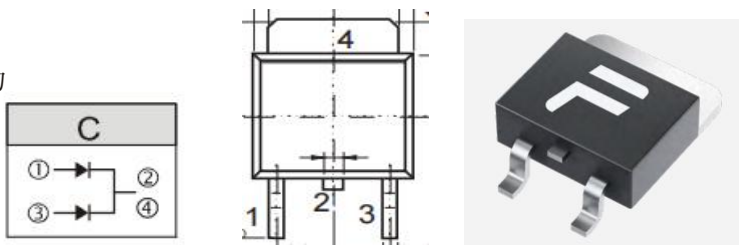
■ Features 特点

High surge current capability 高浪涌电流能力

Low forward voltage drop 低正向压降

High reliability 高可靠性

Case 封装:TO-252



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MBRD 2045	MBRD 2060	MBRD 20100	MBRD 20150	MBRD 20200	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	45	60	100	150	200	V
DC Reverse Voltage 直流反向电压	V_R	45	60	100	150	200	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	32	42	70	105	140	V
Forward Rectified Current 正向整流电流	I_F	20					A
Peak Surge Current 峰值浪涌电流	I_{FSM}	175					A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	8					$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150					$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	$-55\text{to}+150^{\circ}\text{C}$					$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MBRD 2045	MBRD 2060	MBRD 20100	MBRD 20150	MBRD 20200	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	0.70	0.85	0.9		V	I _F =20A
Reverse Current 反向电流	I _R (25℃) (125℃)	0.1 5		0.02 2			mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	500					pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

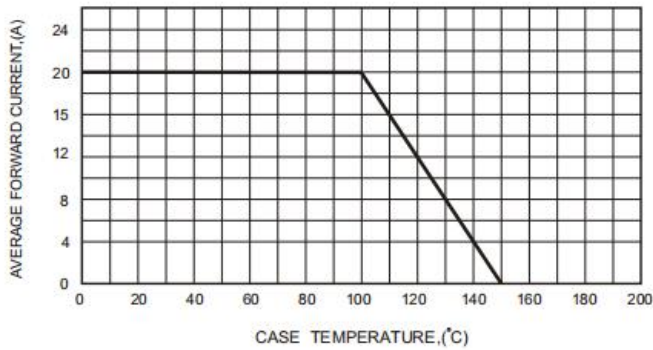


FIG.2-TYPICAL FORWARD CHARACTERISTICS

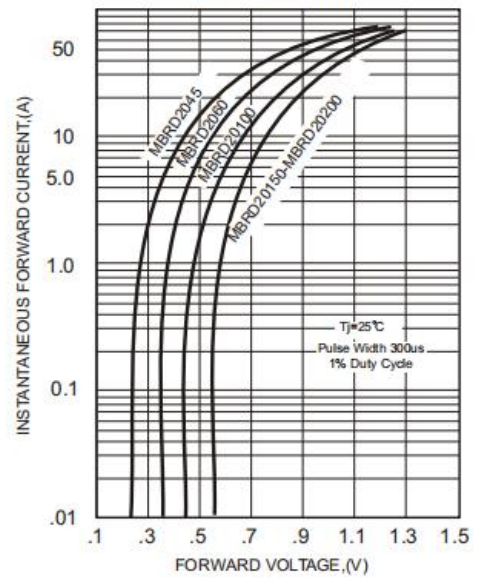


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

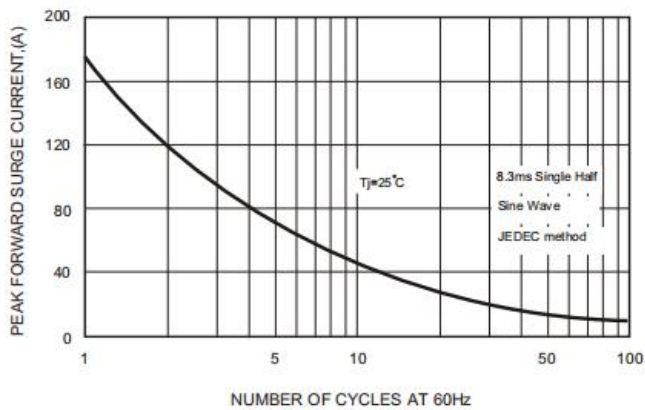


FIG.4-TYPICAL JUNCTION CAPACITANCE

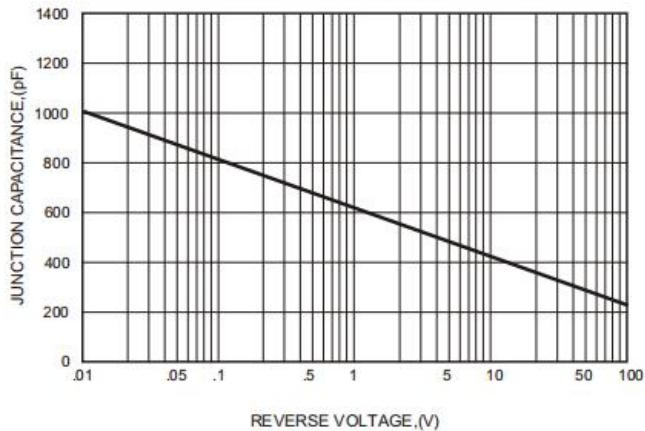
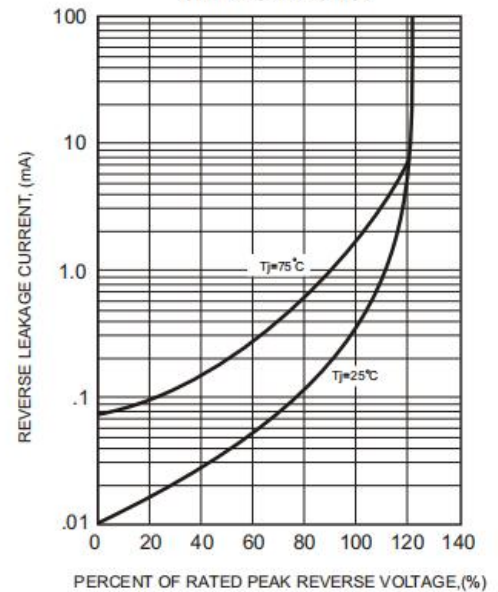


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸

TO-252

Unit: mm

